

### **SN54LS224A, SN74LS224A**

### 16x4 Synchronous First-In, First-Out Memories With 3-State Outputs

The SN54LS224A and SN74LS224A 64-bit, low-power Schottky memories are organized as 16 words by 4 bits each. They can be expanded in multiples of 15m + 1 words or 4n bits, or both (where n is the number of packages in the vertical array and m is the number of packages in the horizontal array); however, some external gating is required. For longer words, the input-ready (IR) signals of the first-rank packages and output-ready (OR) signals of the last-rank packages must be ANDed for proper synchronization.

A first-in, first-out (FIFO) memory is a storage device that allows data to be written to and read from its array at independent data rates. These FIFOs are designed to process data at rates up to 10 MHz in a bit-parallel format, word by word.

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#### **Quality Overview**

- ISO-9001
- AS9120 certification
- Qualified Manufacturers List (QML) MIL-PRF-38535
  - Class Q Military
  - Class V Space Level
- Qualified Suppliers List of Distributors (QSLD)
  - Rochester is a critical supplier to DLA and meets all industry and DLA standards.

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The original manufacturer's datasheet accompanying this document reflects the performance and specifications of the Rochester manufactured version of this device. Rochester Electronics guarantees the performance of its semiconductor products to the original OEM specifications. 'Typical' values are for reference purposes only. Certain minimum or maximum ratings may be based on product characterization, design, simulation, or sample testing.

# SN54LS224A, SN74LS224A $16 \times 4$ SYNCHRONOUS FIRST-IN, FIRST-OUT MEMORIES WITH 3-STATE OUTPUTS

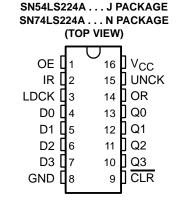
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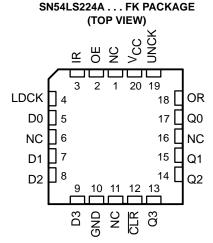
- Independent Synchronous Inputs and Outputs
- 16 Words by 4 Bits Each
- 3-State Outputs Drive Bus Lines Directly
- Data Rates up to 10 MHz
- Fall-Through Time 50 ns Typical
- Data Terminals Arranged for Printed Circuit Board Layout
- Expandable Using External Gating
- Packaged in Standard Plastic (N) and Ceramic (J) 300-mil DIPs, and Ceramic Chip Carriers (FK)

#### description

The SN54LS224A and SN74LS224A 64-bit, low-power Schottky memories are organized as 16 words by 4 bits each. They can be expanded in multiples of 15m + 1 words or 4n bits, or both (where n is the number of packages in the vertical array and m is the number of packages in the horizontal array); however, some external gating is required. For longer words, the input-ready (IR) signals of the first-rank packages and output-ready (OR) signals of the last-rank packages must be ANDed for proper synchronization.

A first-in, first-out (FIFO) memory is a storage device that allows data to be written to and read from its array at independent data rates. These FIFOs are designed to process data at rates up to 10 MHz in a bit-parallel format, word by word.





NC - No internal connection

The load clock (LDCK) normally is held low, and data is written into memory on the high-to-low transition of LDCK. The unload clock (UNCK) normally is held high, and data is read out on the low-to-high transition of UNCK. The memory is full when the number of words clocked in exceeds by 16 the number of words clocked out. When the memory is full, LDCK signals have no effect on the data residing in memory. When the memory is empty, UNCK signals have no effect.

Status of the FIFO memory is monitored by the IR and OR flags that indicate not-full and not-empty conditions. IR is high only when the memory is not full and LDCK is low. OR is high only when the memory is not empty and UNCK is high.

A low level on the clear  $(\overline{CLR})$  input resets the internal stack-control pointers and also sets IR high and OR low to indicate that old data remaining at the data outputs is invalid. Data outputs are noninverting, with respect to the data inputs, and are at high impedance when the output-enable (OE) input is low. OE does not affect the IR and OR outputs.

The SN74LS224A is characterized for operation from 0°C to 70°C. The SN54LS224A is characterized over the full military temperature range of –55°C to 125°C.



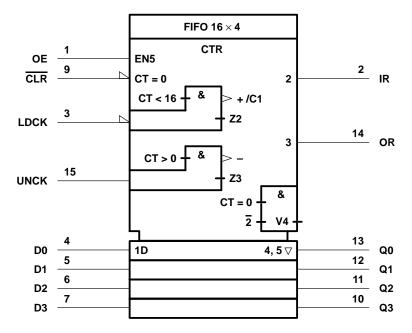
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# SN54LS224A, SN74LS224A $16 \times 4$ SYNCHRONOUS FIRST-IN, FIRST-OUT MEMORIES WITH 3-STATE OUTPUTS

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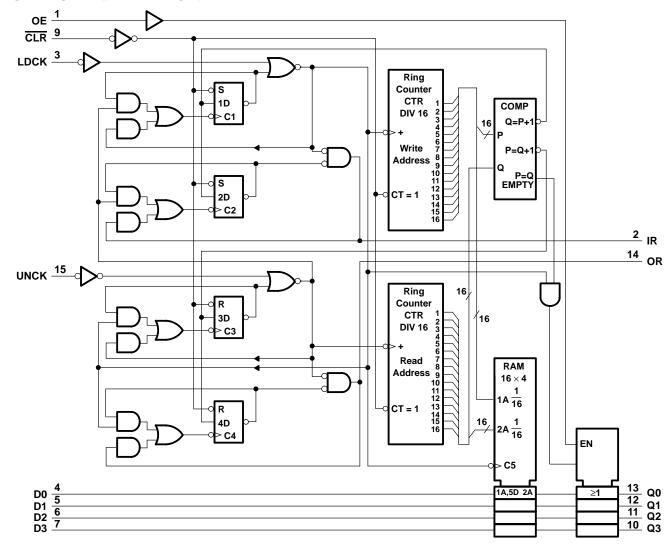
#### logic symbol<sup>†</sup>



<sup>†</sup> This symbol is in accordance with ANSI/IEEE Standard 91-1984 and IEC Publication 617-12. This symbol is functionally accurate but does not show the details of implementation; for these details, see the logic diagram. The symbol represents the memory as if it were controlled by a single counter whose content is the number of words stored at the time. Output data is invalid when the counter content (CT) is 0. Pin numbers shown are for the J and N packages.



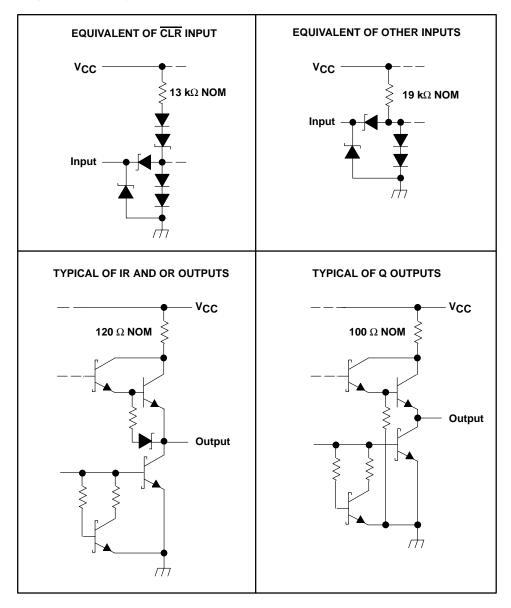
#### logic diagram (positive logic)



Pin numbers shown are for the J and N packages.

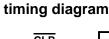
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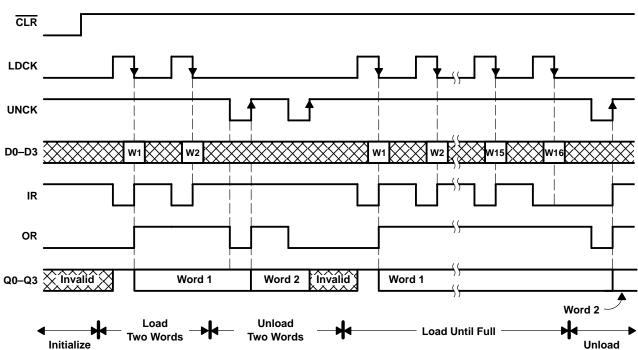
#### schematics of inputs and outputs





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#### absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V <sub>CC</sub> (see Note 1)	–0.5 V to 7 V
Input voltage range, V <sub>I</sub>	–0.5 V to 7 V
Off-state output voltage range, V <sub>O</sub>	
Package thermal impedance, $\theta_{JA}$ : N package (see Note 2)	67°C/W
N package (see Note 3)	88°C/W
Storage temperature range, T <sub>sta</sub>	

<sup>†</sup> Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. All voltage values are with respect to GND.

- 2. The package thermal impedance is calculated in accordance with JESD 51-7.
- 3. The package thermal impedance is calculated in accordance with JESD 51-3.



#### **SN54LS224A, SN74LS224A** 16 × 4 SYNCHRONOUS FIRST-IN, FIRST-OUT MEMORIES WITH 3-STATE OUTPUTS

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#### recommended operating conditions (see Note 4)

			SN54LS224A			SN74LS224A			UNIT
			MIN	NOM	MAX	MIN	NOM	MAX	UNIT
Vcc	Supply voltage		4.5	5	5.5	4.75	5	5.25	V
VIH	V <sub>IH</sub> High-level input voltage		2			2			V
VIL	Low-level input voltage				0.7			0.8	V
la	High-level output current				-1			-2.6	mA
OH F	IR, OR			-0.4			-0.4	IIIA	
lOL	Low level output ourrent	Q outputs			12			24	mA
	Low-level output current IR, OR				4			8	IIIA
T <sub>A</sub>	T <sub>A</sub> Operating free-air temperature		-55		125	0		70	°C

NOTE 4: To ensure proper operation of this high-speed FIFO device, it is necessary to provide a clean signal to the LDCK and UNCK clock inputs. Any excessive noise or glitching on the clock inputs that violates the V<sub>IL</sub>, V<sub>IH</sub>, or minimum pulse-duration limits can cause a false clock or improper operation of the internal read and write pointers.

#### electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS†		SN54LS224A			SN	UNIT		
				MIN	TYP‡	MAX	MIN	TYP‡	MAX	UNII
VIK		$V_{CC} = MIN,$	I <sub>I</sub> = -18 mA			-1.5			-1.5	V
	Q outputs	V <sub>CC</sub> = MIN	$I_{OH} = -2.6 \text{ mA}$				2.4	3.4		V
Vон			$I_{OH} = -1 \mu A$	2.4	3.3					
	IR, OR	$V_{CC} = MIN,$	$I_{OH} = -0.4 \text{ mA}$	2.5	3.4		2.7	3.4		
	Opurtourto	\/ MINI	I <sub>OL</sub> = 12 mA		0.25	0.4		0.25	0.4	
\/a.	Q outputs V <sub>CC</sub> = MIN	ACC = IMILIA	$I_{OL} = 24 \text{ mA}$					0.35	0.5	V
VOL	IR, OR	V <sub>CC</sub> = MIN	I <sub>OL</sub> = 4 mA		0.25	0.4		0.25	0.4	
			IOL = 8 mA					0.35	0.5	
lozh	Q outputs	$V_{CC} = MAX$ ,	V <sub>O</sub> = 2.7 V			20			20	μΑ
lozL	Q outputs	$V_{CC} = MAX$ ,	V <sub>O</sub> = 0.4 V			-20			-20	μΑ
lį		$V_{CC} = MAX$ ,	V <sub>I</sub> = 7 V			0.1			0.1	mA
lіН		$V_{CC} = MAX$ ,	V <sub>I</sub> = 2.7 V			20			20	μΑ
Ι <sub>Ι</sub> L		$V_{CC} = MAX$ ,	V <sub>I</sub> = 0.4 V			-0.4			-0.4	mA
	Q outputs	W. MAY		-30		-130	-30		-130	A
los§	IR, OR	V <sub>CC</sub> = MAX		-20		-100	-20		-100	mA
	VCC = MAX		Outputs high		84	135		84	135	
ICC		$V_{CC} = MAX$	Outputs low		87	155		87	155	<b></b>
			Outputs disabled		89	155		89	155	

<sup>†</sup> For conditions shown as MIN or MAX, use the appropriate value specified under recommended operating conditions.



<sup>‡</sup> All typical values are at  $V_{CC} = 5 \text{ V}$ ,  $T_A = 25^{\circ}\text{C}$ .

<sup>9</sup> Not more than one output should be shorted at a time, and duration of the short circuit should not exceed one second.

# SN54LS224A, SN74LS224A $16 \times 4$ SYNCHRONOUS FIRST-IN, FIRST-OUT MEMORIES WITH 3-STATE OUTPUTS

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#### timing requirements over recommended operating conditions (see Note 4 and Figure 1)

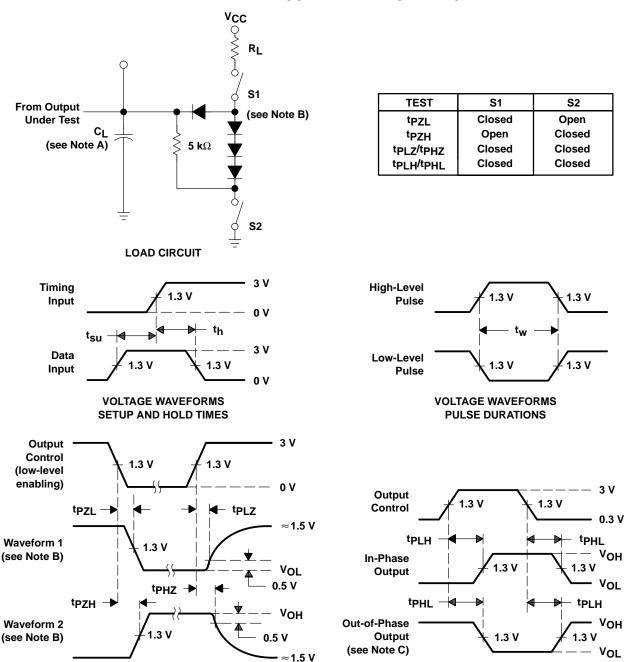
					SN74LS224A		UNIT	
					MIN	MAX	UNII	
		LDCK high	60		60			
t <sub>W</sub> Pulse duration		LDCK low	15		15		ns	
	Pulse duration	UNCK low	30		30			
	UNCK high	30		30				
		CLR low	20		20			
	Setup time	Data to LDCK↓	50		50			
t <sub>su</sub>		LDCK↓ before UNCK↓	50		50		ns	
		UNCK↑ before LDCK↑	50		50			
t <sub>h</sub>	Hold time	Data from LDCK↓	0		10	·	ns	

NOTE 4: To ensure proper operation of this high-speed FIFO device, it is necessary to provide a clean signal to the LDCK and UNCK clock inputs. Any excessive noise or glitching on the clock inputs that violates the V<sub>IL</sub>, V<sub>IH</sub>, or minimum pulse-duration limits can cause a false clock or improper operation of the internal read and write pointers.

### switching characteristics, $V_{CC}$ = 5 V, $T_A$ = 25°C (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)		TEST CONDITIONS		TYP	MAX	UNIT
t <sub>PLH</sub>	LDCK↓	IR	$R_1 = 2 k\Omega$	C 15 pE		25	40	ns
tPHL	LDCK <sup>↑</sup>	IK.	RL = 2  KS2,	CL = 15 pr		36	50	
t <sub>PLH</sub>	LDCK↓	OR	$R_L = 2 k\Omega$ ,	C <sub>L</sub> = 15 pF		48	70	ns
<sup>t</sup> PLH	UNCK1	OR	P 2 kO	C 15 pE		29	45	
t <sub>PHL</sub>	UNCK↓	UK	$R_L = 2 k\Omega$ ,	C[ = 15 pr		28	45	ns
t <sub>PLH</sub>	UNCK↑	IR	$R_L = 2 k\Omega$ ,	C <sub>L</sub> = 15 pF		49	70	ns
t <sub>PLH</sub>		IR	$R_L = 2 k\Omega$	0: 45 =5		36	55	ns
t <sub>PHL</sub>	CLR↓	OR	$\int K L = 2 K \Sigma Z,$	CL = 15 pr		25	40	
tPHL	LDCK↓	Q	$R_L = 667 \Omega$ ,	C <sub>L</sub> = 45 pF		34	50	ns
<sup>t</sup> PLH	LINOK↑	Q	D 667.0	C <sub>L</sub> = 45 pF	54	80	20	
t <sub>PHL</sub>	UNCK↑	Q	K[ = 007 12,			45	70	ns
<sup>t</sup> PZL	OE↑	Q $R_1 = 667 \Omega$ , $C_1 = 45 pF$	22	35	no			
<sup>t</sup> PZH	OET	Q	KL = 007 12,	CL = 45 pr		21	35	ns
tPLZ	OE↓	Q	$R_L = 667 \Omega$ , $C_L = 5 pF$		16	30	no	
<sup>t</sup> PHZ	OL*	N <sub>L</sub> = 007 22, C <sub>L</sub> = 5 pr		OL = 3 pr		18	30	ns

#### PARAMETER MEASUREMENT INFORMATION



- NOTES: A.  $C_L$  includes probe and jig capacitance.
  - B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.

**VOLTAGE WAVEFORMS** 

**PROPAGATION DELAY TIMES** 

- C. All input pulses have the following characteristics: PRR  $\leq$  1 MHz,  $t_{\Gamma}$  < 15 ns,  $t_{f}$  < 6 ns,  $Z_{O} \approx$  50  $\Omega$ .
- D. All diodes are 1N916 or 1N3064.

**VOLTAGE WAVEFORMS** 

**ENABLE AND DISABLE TIMES, 3-STATE OUTPUTS** 

E. The outputs are measured one at a time with one transition per measurement.

Figure 1. Load Circuits and Voltage Waveforms



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